

Optical nanocrystallography with tip-enhanced phonon Raman spectroscopy

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Here we present supplementary material to our letter. The specific Raman selection rules are derived for BaTiO₃ in the experimental geometry taking into account the symmetry selectivity of the Raman response and the polarization-dependent field enhancement of the tip. We calculate the experimental Raman enhancement.

Phonon TERS Selection rules

The Raman tensors for the $4mm$ space group for BaTiO₃ with the crystallographic c -axis along the z -direction, excluding the weak mode of B₁ symmetry are given by¹:

$$\mathbf{A}_1(z) = \begin{pmatrix} a & 0 & 0 \\ 0 & a & 0 \\ 0 & 0 & b \end{pmatrix}, \mathbf{E}(x) = \begin{pmatrix} 0 & 0 & c \\ 0 & 0 & 0 \\ c & 0 & 0 \end{pmatrix}, \mathbf{E}(y) = \begin{pmatrix} 0 & 0 & 0 \\ 0 & 0 & c \\ 0 & c & 0 \end{pmatrix},$$

with x , y , and z denoting the phonon polarization directions along the corresponding crystallographic axes as seen in Fig. 1c. The tip enhancement tensors F'_{ij} and F'_{kl} take, e.g., for

$\mathbf{q} = \mathbf{k}_i - \mathbf{k}_s$	mode	$\mathbf{k}_i(e_i e_s)\mathbf{k}_s$	I_{TERS}	domain
$\mathbf{q} \parallel z$	A ₁ LO	$z(\overline{yy})\overline{z} = p_{\text{in}}p_{\text{out}}$	$\propto a_{LO} ^2(F_p F'_p)^2$	c
$\mathbf{q} \parallel y$	A ₁ TO	$y(\overline{xx})\overline{y} = p_{\text{in}}p_{\text{out}}$	$\propto c_{TO} ^2(F_p F'_p)^2$	$a_{y'}$
"	E TO	$y(\overline{xz})\overline{y} = p_{\text{in}}s_{\text{out}}$	$\propto c_{TO} ^2(F_s F'_p)^2$	"
"	E TO	$y(\overline{zx})\overline{y} = s_{\text{in}}p_{\text{out}}$	$\propto c_{TO} ^2(F_p F'_s)^2$	"
$\mathbf{q} \parallel x$	A ₁ TO	$x(\overline{zz})\overline{x} = p_{\text{in}}p_{\text{out}}$	$\propto b_{TO} ^2(F_p F'_p)^2$	$a_{x'}$
"	E TO	$x(\overline{zy})\overline{x} = p_{\text{in}}s_{\text{out}}$	$\propto c_{TO} ^2(F_s F'_p)^2$	"
"	E TO	$x(\overline{yz})\overline{x} = s_{\text{in}}p_{\text{out}}$	$\propto c_{TO} ^2(F_p F'_s)^2$	"

TABLE I: **TERS selection rules for tetragonal BaTiO₃**. Here a rod is oriented parallel to the incident and scattered light. For each domain, the crystal coordinates are rotated to reflect the change in ferroelectric orientation (i.e. $c \parallel z$). Contributions under the weakly enhanced $s_{\text{in}}s_{\text{out}}$ configuration, or under oblique incidence (weak E LO mode) are neglected.

the specific lab frame coordinates depicted in Fig. 1a, the form of:

$$\mathcal{F}_{ij}^{\text{TERS}} = \begin{pmatrix} F_s & 0 & 0 \\ 0 & F_p & 0 \\ 0 & 0 & 0 \end{pmatrix}, \quad \mathcal{F}'_{kl}{}^{\text{TERS}} = \begin{pmatrix} F'_s & 0 & 0 \\ 0 & F'_p & 0 \\ 0 & 0 & 0 \end{pmatrix},$$

The indices represent detected output and incident polarization, with p and s polarization defined as parallel and perpendicular with respect to the plane formed by the tip axis and incident or scattered k -vectors, respectively. The diagonal nature of our tensors reflects the lack of depolarized near-field Raman signal² observed with our tips. $F_p \simeq F'_p$ and $F_s \simeq F'_s$ because the amount of phonon Raman shift is in general less than or at most comparable to the plasmon linewidth³.

For a backscattering geometry with the incident and Raman-scattered k -vectors assumed parallel with respect to the sample surface to approximate the experimental configuration (Fig. 1a), Table I shows the resulting TERS selection rules for three distinct crystallographic orientations representing the three possible orthogonal ferroelectric domain configurations. The expected TERS signal I_{TERS} under the different polarization conditions is obtained by transforming \mathcal{F}_{ij} and \mathcal{F}'_{kl} into the corresponding crystal coordinates. Modes only present under the weakly enhanced $s_{\text{in}}s_{\text{out}}$ configuration (e.g., A₁ LO for c-domain) have been omit-

ted, as well as the E LO mode, which is weak and its excitation only possible under oblique angle of incidence (e.g., $\mathbf{q} \parallel x$ and $x(zx)\bar{x}$)¹.

Enhancement factor

The underlying Raman tip-enhancement can be derived from the distance dependence and lateral scan of Fig. 2. We estimate $\sim 1 - 5$ BaTiO₃ nanocrystals within the laser focus contributing to the far-field response based on nanocrystal surface density. With a near-field probe volume of $\sim 10^3 \text{ nm}^3$, as determined to first order by the tip apex radius $r \sim 10 - 20$ nm, and with nanorod dimensions of $\sim 2 \mu\text{m} \times 300 \text{ nm} \times 35 \text{ nm}$ this corresponds to a Raman enhancement of $I \sim 10^4 - 10^5$. With $I \propto |E|^4$ this value is consistent with the typical field enhancement of the tips of order 10–20 as determined previously⁴ in the absence of plasmonic tip-sample coupling.

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- ¹ DiDomenico, M., Wemple, S. H. & Porto, S. P. S. Raman spectrum of single-domain BaTiO₃. *Phys. Rev.* **174**, 522–530 (1968).
 - ² Ossikovski, R., Nguyen, Q. & Picardi, G. Simple model for the polarization effects in tip-enhanced Raman spectroscopy. *Phys. Rev. B* **75**, 045412 (2007).
 - ³ Neacsu, C. C., Dreyer, J., Behr, N. & Raschke, M. B. Scanning-probe Raman spectroscopy with single-molecule sensitivity. *Phys. Rev. B* **73**, 193406 (2006).
 - ⁴ Neacsu, C. C., Reider, G. A. & Raschke, M. B. Second-harmonic generation from nanoscopic metal tips: Symmetry selection rules for single asymmetric nanostructures. *Phys. Rev. B* **71**, 201402 (2005).